

IN THE CLAIMS

Please amend the claims as follows.

1. (Amended) A method comprising:

forming a first dielectric layer above a first structure layer;

A4

forming a first opening in the first dielectric layer;

forming a first copper layer above the first dielectric layer and in the first opening; and

measuring an actual thickness of the copper layer, measuring the actual thickness comprises averaging a plurality of thicknesses from a plurality of locations on said first copper layer;

comparing the actual thickness to a desired thickness; and

varying at least one parameter used to form the first copper layer in response to the actual thickness differing from the desired thickness, wherein varying at least one parameter comprises varying an amount of time that the first copper layer is electroplated above the first dielectric layer and in the first opening.

22. (Amended) A system, comprising:

A5

means for forming a first dielectric layer above a first structure layer;

means for forming a first opening in the first dielectric layer;

means for forming a first copper layer above the first dielectric layer and in the first opening;

means for measuring an actual thickness of the copper layer, measuring the actual thickness comprises averaging a plurality of thicknesses from a plurality of locations on said first copper layer;

A⁵

means for comparing the actual thickness to a desired thickness; and

means for varying at least one parameter used to form the first copper layer in response to the actual thickness differing from the desired thickness, wherein varying at least one parameter comprises varying an amount of time that the first copper layer is electroplated above the first dielectric layer and in the first opening.
